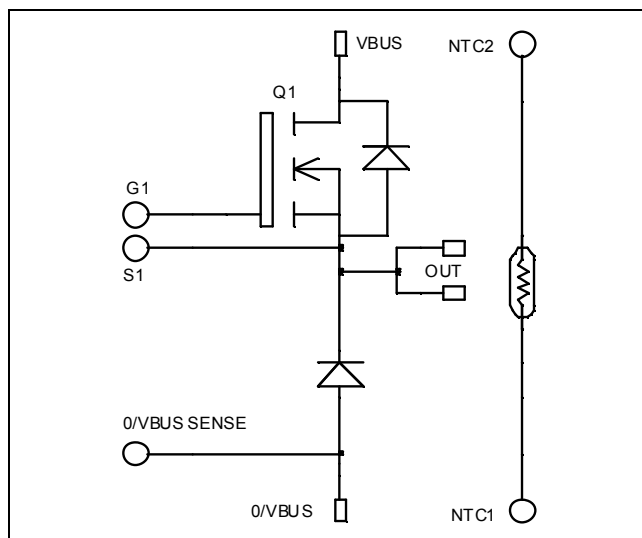


Buck chopper MOSFET Power Module

$$V_{DSS} = 100V$$

$$R_{DSon} = 4.5m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 278A \text{ @ } T_c = 25^\circ C$$



Application

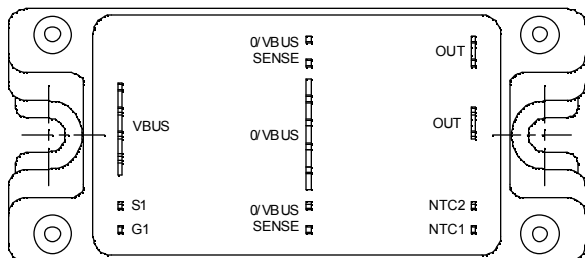
- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS V[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	100	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$ 278	A
		$T_c = 80^\circ C$ 207	
I_{DM}	Pulsed Drain current	1100	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	5	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$ 780	W
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$	$T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0V, V_{DS} = 80V$	$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 125A$			4.5	5	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$		2		4	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$				± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$			20		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$			8		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$			2.9		
Q_g	Total gate Charge	$V_{GS} = 10V$			700		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 50V$			120		
Q_{gd}	Gate – Drain Charge	$I_D = 250A$			360		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching $V_{GS} = 15V$ $V_{Bus} = 66V$ $I_D = 250A$ $R_G = 2.5\Omega$			80		ns
T_r	Rise Time				165		
$T_{d(off)}$	Turn-off Delay Time				280		
T_f	Fall Time				135		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 250A, R_G = 2.5\Omega$			1.1		mJ
E_{off}	Turn-off Switching Energy ❷				1.2		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 250A, R_G = 2.5\Omega$			1.22		mJ
E_{off}	Turn-off Switching Energy ❷				1.28		

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =200V	T _j = 25°C			350	μA
			T _j = 125°C			600	
I _{F(AV)}	Maximum Average Forward Current	50% duty cycle	T _c = 80°C		200		A
V _F	Diode Forward Voltage	I _F = 200A			1		V
		I _F = 400A			1.4		
		I _F = 200A	T _j = 125°C		0.9		
t _{rr}	Reverse Recovery Time	I _F = 200A V _R = 133V di/dt =400A/μs	T _j = 25°C		60		ns
			T _j = 125°C		110		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		400		nC
			T _j = 125°C		1680		

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case	Transistor			0.16	°C/W
		Diode			0.29	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To Heatsink	M5	1.5	4.7	N.m
Wt	Package Weight				160	g

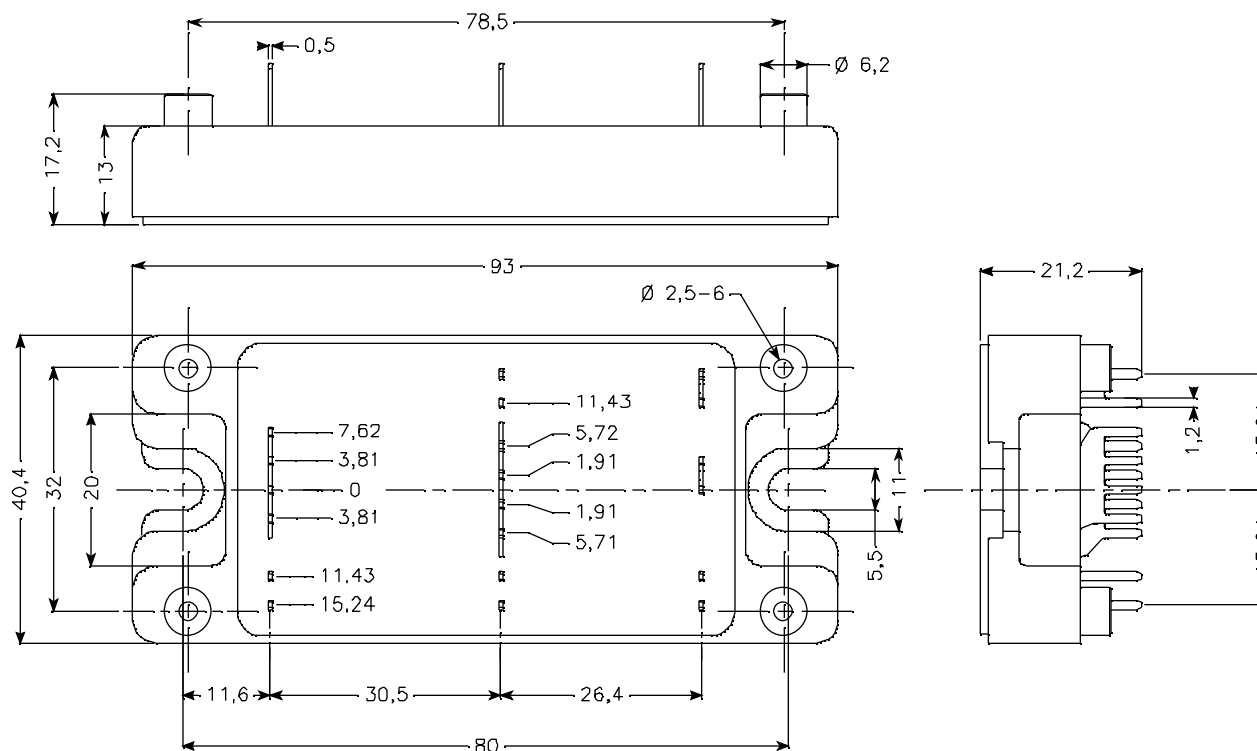
Temperature sensor NTC (see application note APT0406 on www.advancedpower.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

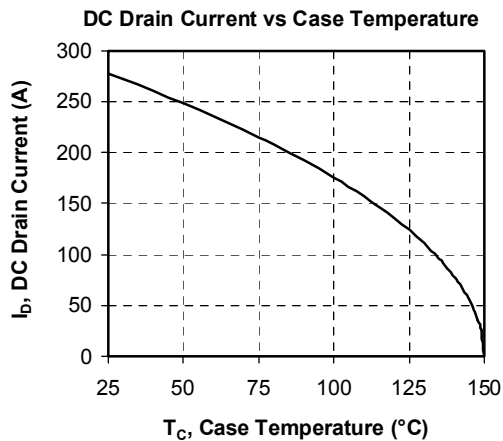
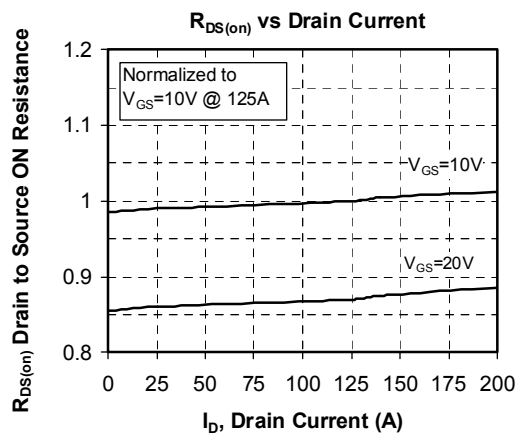
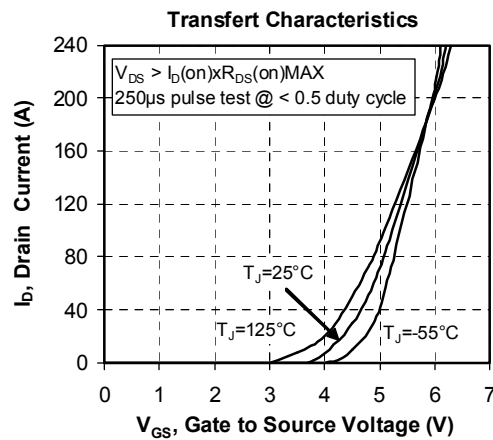
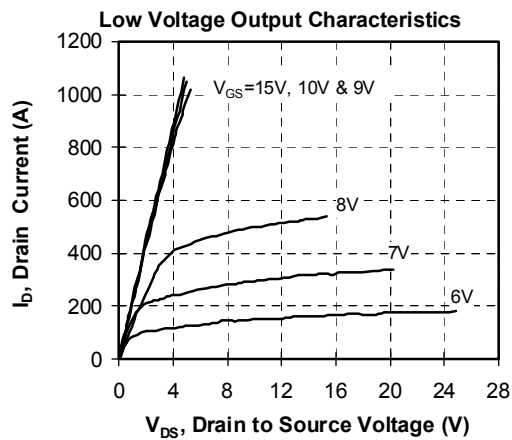
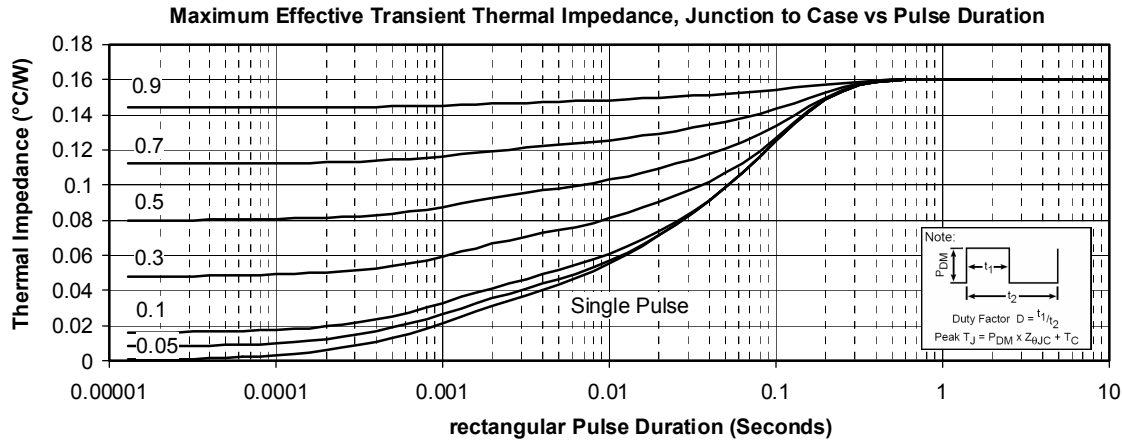
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

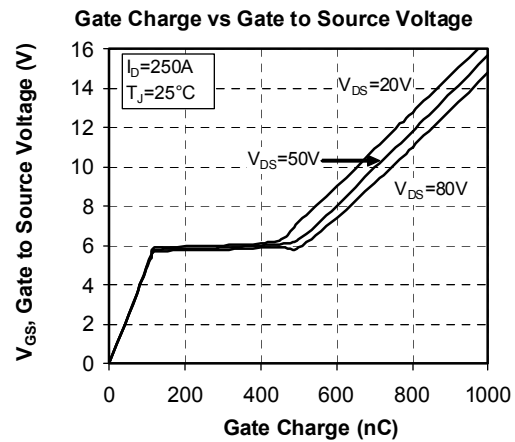
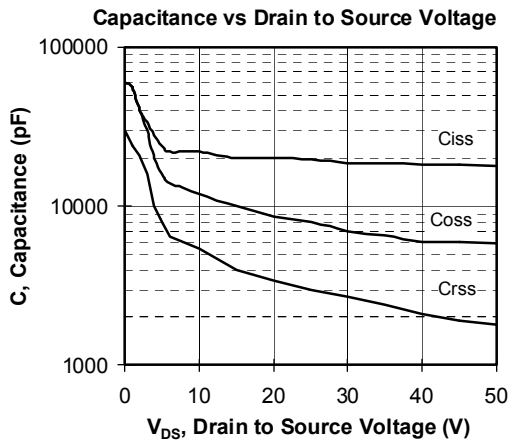
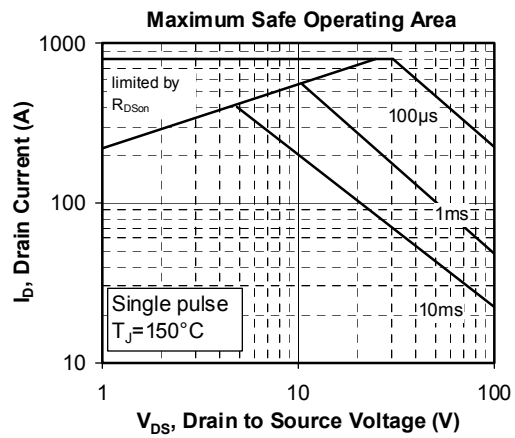
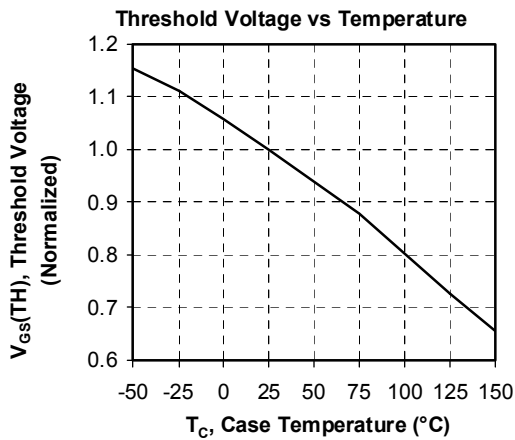
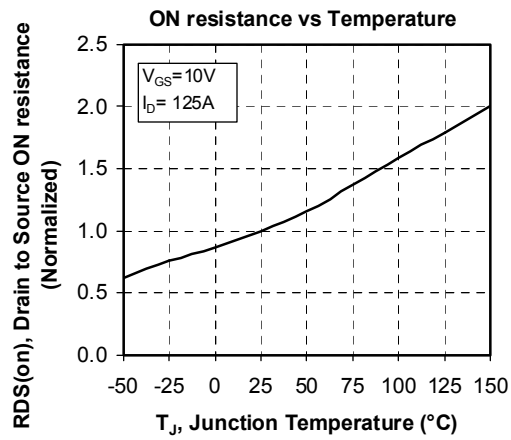
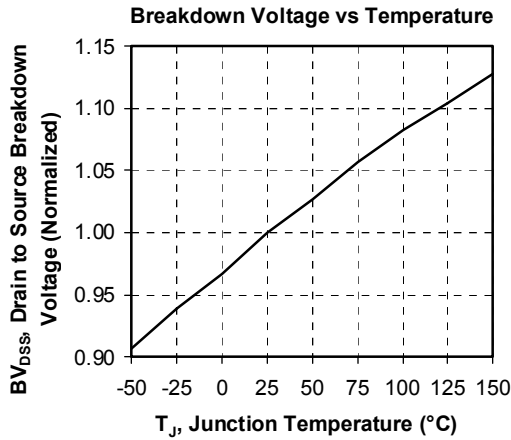
T: Thermistor temperature
R_T: Thermistor value at T

Package outline (dimensions in mm)

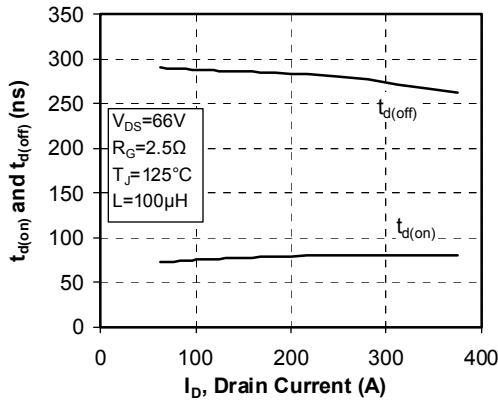


Typical Performance Curve

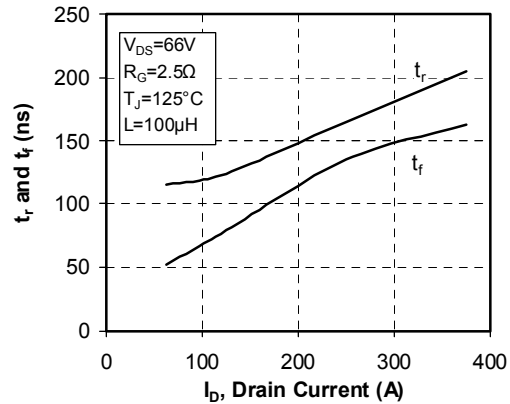




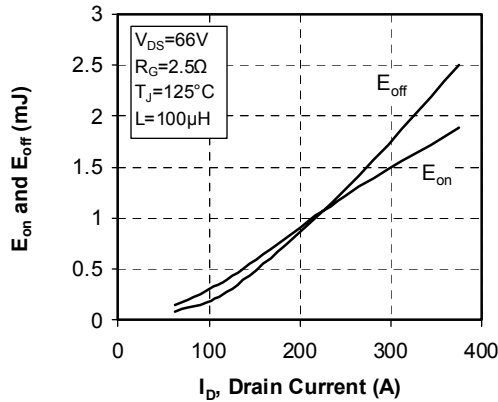
Delay Times vs Current



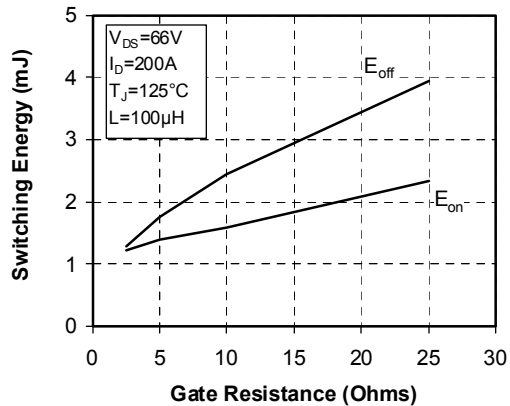
Rise and Fall times vs Current



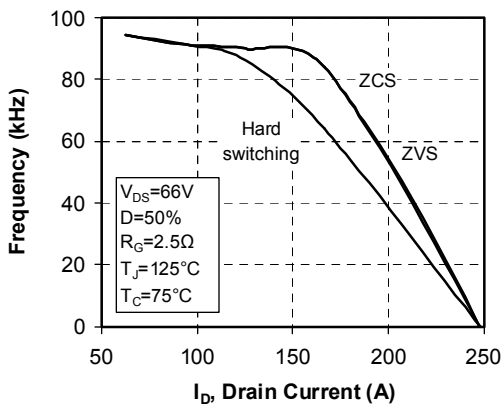
Switching Energy vs Current



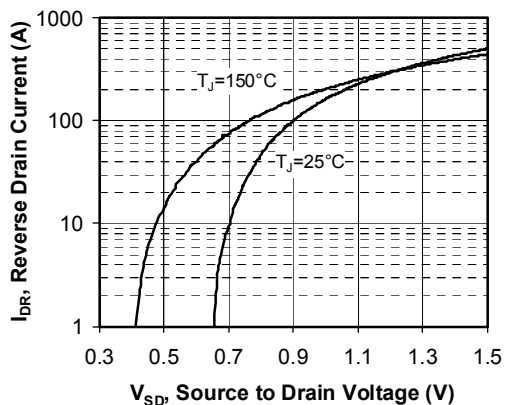
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.